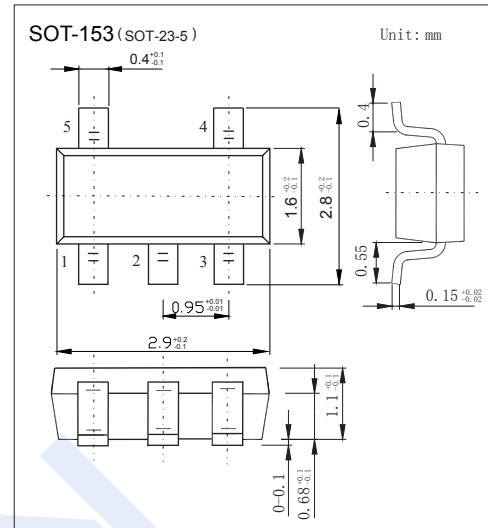
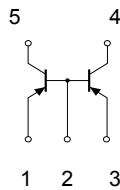


PNP Transistors

FMS4 (KMS4)

■ Features

- Collector Current Capability $I_c = -50\text{mA}$
- Collector Emitter Voltage $V_{CE0} = -120\text{V}$
- High breakdown voltage.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|--------------------------------|-----------|------------|------------------|
| Collector - Base Voltage | V_{CB0} | -120 | V |
| Collector - Emitter Voltage | V_{CE0} | -120 | |
| Emitter - Base Voltage | V_{EB0} | -5 | |
| Collector Current - Continuous | I_c | -50 | mA |
| Collector Power Dissipation | P_c | 300 | mW |
| Junction Temperature | T_J | 150 | $^\circ\text{C}$ |
| Storage Temperature range | T_{stg} | -55 to 150 | |

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|--------------------------------------|---------------|---|------|-----|------|---------------|
| Collector- base breakdown voltage | V_{CB0} | $I_c = -100\ \mu\text{A}$, $I_E = 0$ | -120 | | | V |
| Collector- emitter breakdown voltage | V_{CE0} | $I_c = -1\ \text{mA}$, $I_B = 0$ | -120 | | | |
| Emitter - base breakdown voltage | V_{EB0} | $I_E = -100\ \mu\text{A}$, $I_c = 0$ | -5 | | | |
| Collector-base cut-off current | I_{CB0} | $V_{CB} = -100\ \text{V}$, $I_E = 0$ | | | -0.5 | μA |
| Emitter cut-off current | I_{EB0} | $V_{EB} = -4\ \text{V}$, $I_c = 0$ | | | -0.5 | |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_c = -10\ \text{mA}$, $I_B = -1\ \text{mA}$ | | | -0.5 | V |
| Base - emitter saturation voltage | $V_{BE(sat)}$ | $I_c = -10\ \text{mA}$, $I_B = -1\ \text{mA}$ | | | -1.2 | |
| DC current gain | h_{FE} | $V_{CE} = -6\ \text{V}$, $I_c = -2\ \text{mA}$ | 180 | | 820 | |
| Transition frequency | f_T | $V_{CE} = -12\ \text{V}$, $I_E = 2\ \text{mA}$, $f = 100\ \text{MHz}$ | | 140 | | MHz |

■ Marking

| Marking | S4 |
|---------|----|
|---------|----|